



General Description:

- (1) Chip Dimension
 Chip Size= 7 mil x 9 mil (180um x 230um)
 Chip Thickness= 90±10 µm
 P/N Bonding Pad= 70±5 µm
- (2) Electrode:
 P (Anode) → Au
 N (Cathode) → Au
- (3) Structure:
 Refer to drawing
 SiO₂ Passivated surface

Electro-optical Characteristics(Ta=RT)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Luminous Intensity	I _v	-	20	-	mcd	I _F = 5mA
		-	60	-	mcd	I _F =20mA
Dominant Wavelength	λ _D	-	460	-	nm	I _F = 5mA
		-	460	-	nm	I _F =20mA
Forward Voltage	V _F	-	3.0	-	V	I _F = 5mA
		-	3.4	-	V	I _F =20mA
Reverse Current	IR	0	-	2	µA	VR=-5V

Features:

1. High Luminous Intensity
2. Long Operation Life
3. High Current; Pulse Operation
4. Indoor/Outdoor Applications

Notes:

1. Dominant wavelength includes an error of ± 1nm
2. Luminous intensity includes an error of ±10%
3. Luminous intensity is measured on bare chip
4. InGaN LED is sensitive to ESD

